1. Record Nr. UNINA990009310590403321

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| Autore | Brooks, Christopher N. |
| Titolo | Architectural acoustics / Christopher N. Brooks |
| Pubbl/distr/stampa | Jefferson, N.C. ; London : McFarland & Company Inc., 2003 |
| ISBN | 978-0-7864-1398-0 |
| Descrizione fisica | VII, 147 p. : ill. ; 23 cm |
| Disciplina | 729.2 |
| Locazione | FINBC |
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| Lingua di pubblicazione | Inglese |
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2. Record Nr. UNISALENTO991003563909707536

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| Autore | Birkhead, Mike |
| Titolo | The survival factor / Mike and Tim Birkhead |
| Pubbl/distr/stampa | London : Boxtree, 1989 |
| ISBN | 1852832452 |
| Edizione | [1st ed.] |
| Descrizione fisica | 208 p. : col. ill. ; 25 cm |
| Altri autori (Persone) | Birkhead, T. R.author |
| Disciplina | 591.5 |
| Soggetti | Environment - Adaptation of animals |
| Lingua di pubblicazione | Inglese |
| Formato | Materiale a stampa |
| Livello bibliografico | Monografia |
| Note generali | Includes index |

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| 3. Record Nr. | UNINA9910830743503321 |
| Titolo | Beyond-CMOS : state of the art and trends / / edited by Alessandro Cresti |
| Pubbl/distr/stampa | London, England : , : ISTE Ltd and John Wiley & Sons, Inc., , [2023]<br>©2023 |
| ISBN | 1-394-22871-6<br>1-394-22869-4 |
| Edizione | [First edition.] |
| Descrizione fisica | 1 online resource (443 pages) |
| Disciplina | 621.381 |
| Soggetti | Digital electronics |
| Lingua di pubblicazione | Inglese |
| Formato | Materiale a stampa |
| Livello bibliografico | Monografia |
| Nota di bibliografia | Includes bibliographical references and index. |
| Nota di contenuto | Cover -- Title Page -- Copyright Page -- Contents -- Preface -- Chapter 1. Tunnel Field-Effect Transistors Based on III-V Semiconductors -- 1.1. Introduction -- 1.2. Experiments -- 1.3. Simulation of III-V-based TFETs -- 1.3.1. The k.p model in the NEGF formalism -- 1.4. SS degradation mechanisms -- 1.4.1. Electrostatic integrity -- 1.4.2. Trap-assisted tunneling -- 1.4.3. Surface roughness -- 1.5. Strategies to improve the on-state current -- 1.5.1. Strain -- 1.5.2. Broken-gap hetero-structures -- 1.5.3. Molar fraction grading of the source material -- 1.6. Conclusion -- 1.7. References -- Chapter 2. Field-Effect Transistors Based on 2D Materials: A Modeling Perspective -- 2.1. Introduction -- 2.1.1. Future of Moore's law -- 2.1.2. The potential of 2D materials -- 2.2. Modeling approach -- 2.2.1. Requirements and state of the art -- 2.2.2. Maximally localized Wannier functions (MLWFs) -- 2.2.3. Towards ab initio quantum transport simulations -- 2.3. 2D device performance analysis -- 2.3.1. MoS2 and other TMDs -- 2.3.2. Novel 2D materials -- 2.4. Challenges and opportunities -- 2.4.1. Electrical contacts between metals and 2D monolayers -- 2.4.2. 2D mobility limiting factors -- 2.4.3. 2D oxides -- 2.4.4. Advanced logic concepts -- 2.5. Conclusion and outlook -- 2.6. Acknowledgments -- 2.7. References -- Chapter 3. Negative Capacitance Field-Effect Transistors -- 3.1. Introduction -- 3.2. The rise of NC-FETs -- 3.3. Understanding NC-FETs from scratch -- 3.3.1. |

Sommario/riassunto

Recent advances in physics, material sciences and technology have allowed the rise of new paradigms with bright prospects for digital electronics, going beyond the reach of Moore's law, which details the scaling limit of electronic devices in terms of size and power. This book presents original and innovative topics in the field of beyond CMOS electronics, ranging from steep slope devices and molecular electronics to spintronics, valleytronics, superconductivity and optical chips. Written by globally recognized leading research experts, each chapter of this book will provide an introductory overview of their topic and illustrate the state of the art and future challenges. Aimed not only at students and those new to this field, but also at well-experienced researchers, Beyond-CMOS provides extremely clear and exciting perspectives about the technology of tomorrow, and is thus an effective tool for understanding and developing new ideas, materials and architectures.